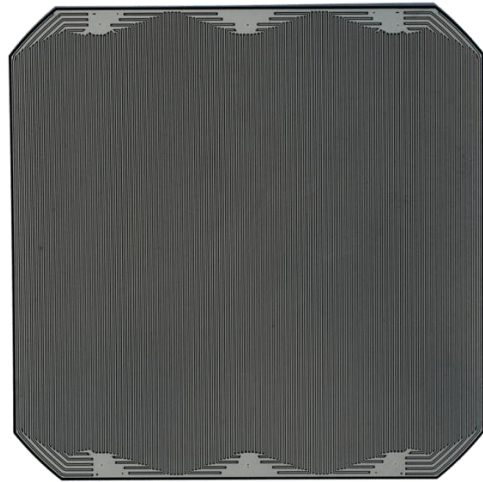
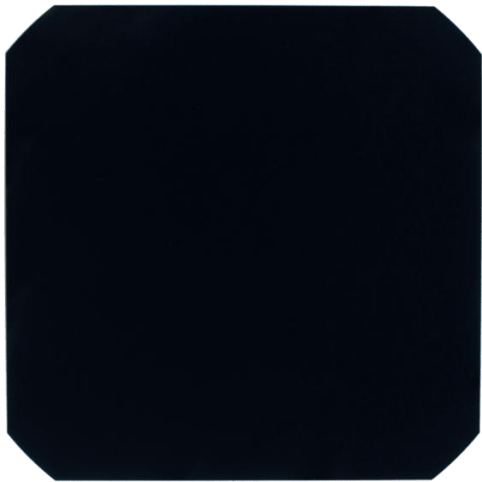


**SUPSI**

# Overview of recent technological development



Mauro Caccivio

SUPSI PVLab Industry day 2026

Mendrisio, 21.05.2026

## The evolution of photovoltaic modules from the 1980s to the present day



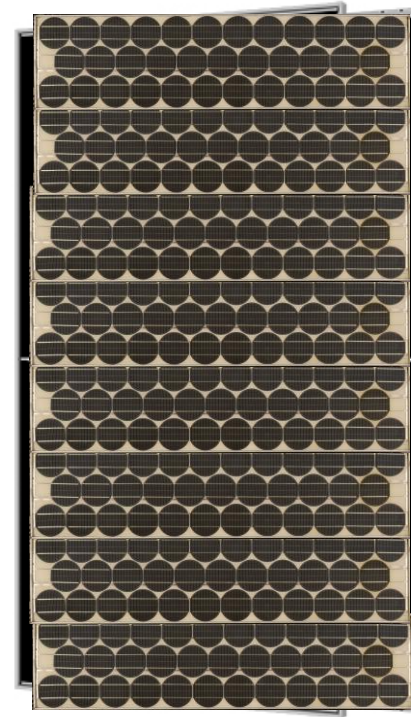
1982: 35W



2012: 240W

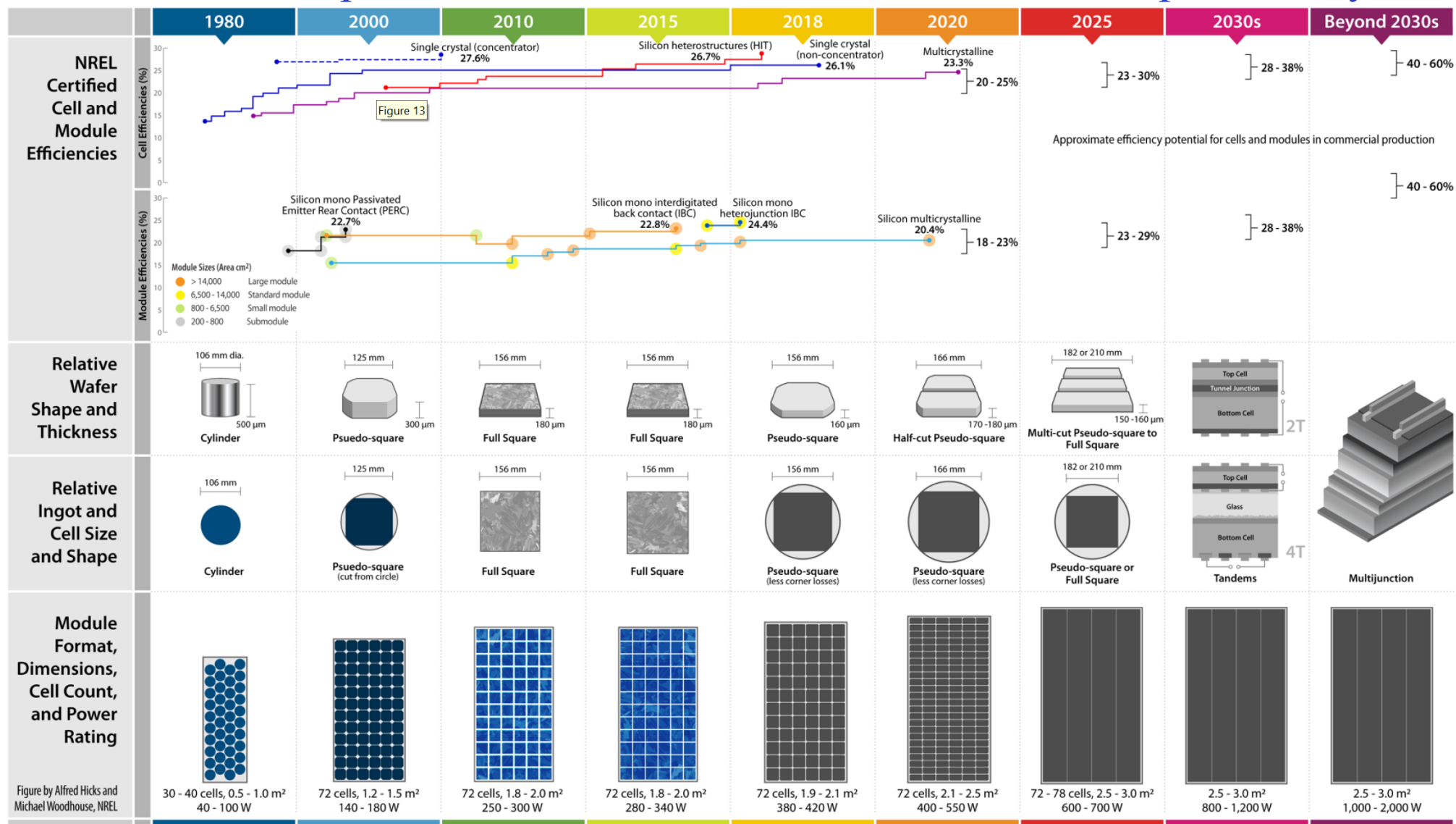


2018: 320W

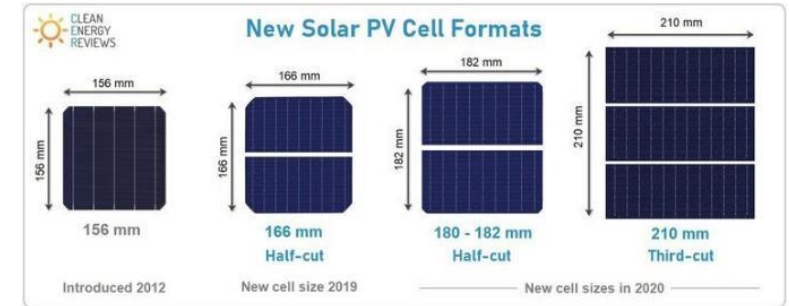
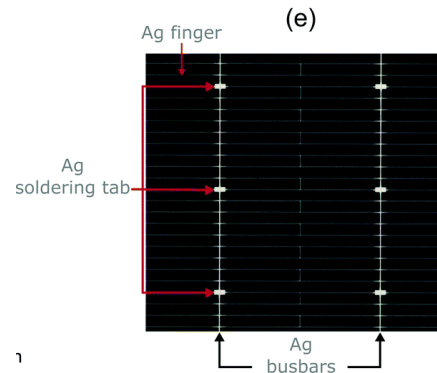
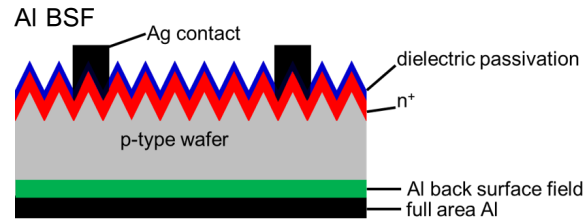
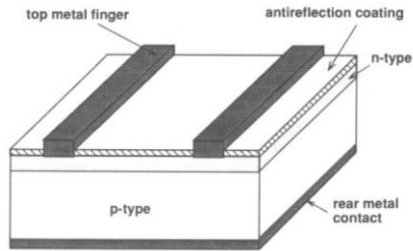


2026: 800W

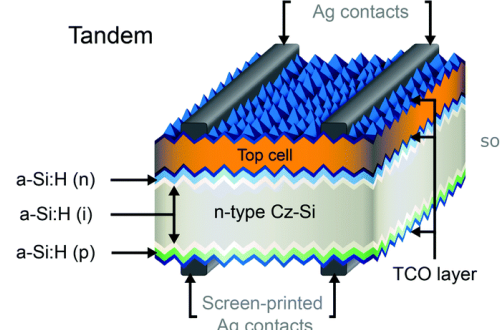
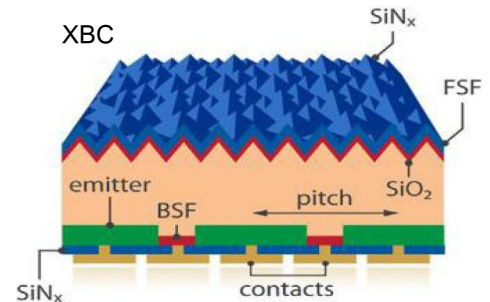
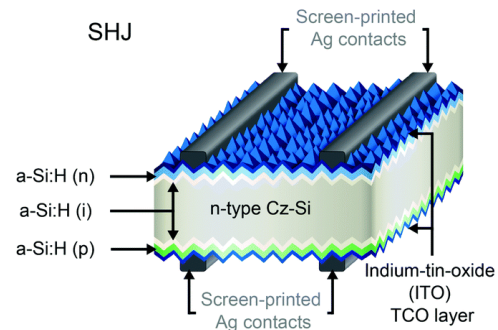
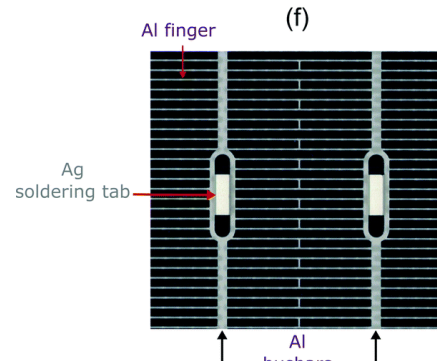
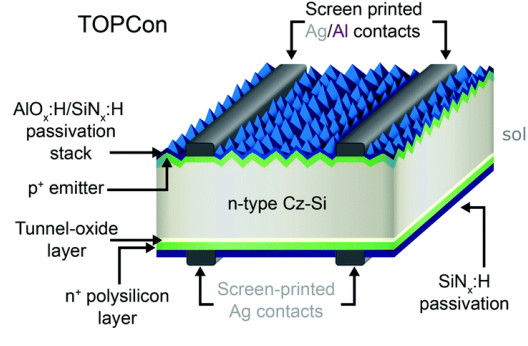
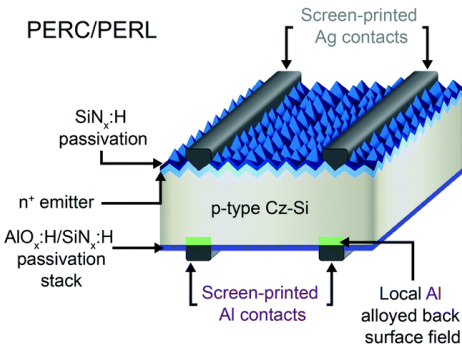
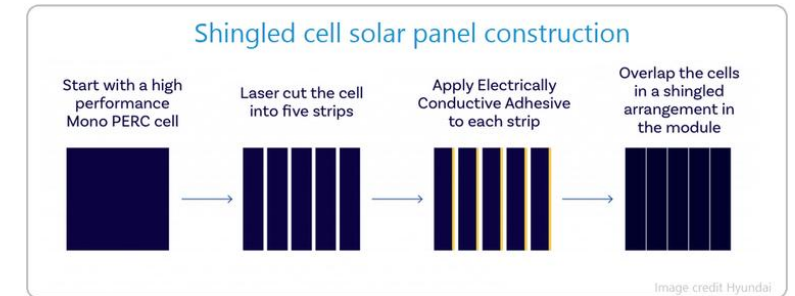
# The evolution of photovoltaic modules from the 1980s to the present day



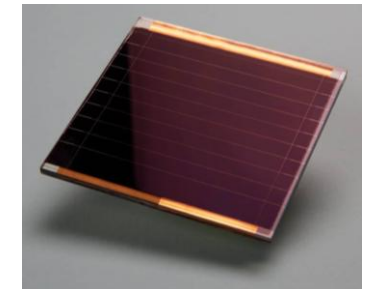
# The evolution of photovoltaic cells



Larger cells divided into several sections; various solutions for electrical contacts



The near future lies in thin-film technology

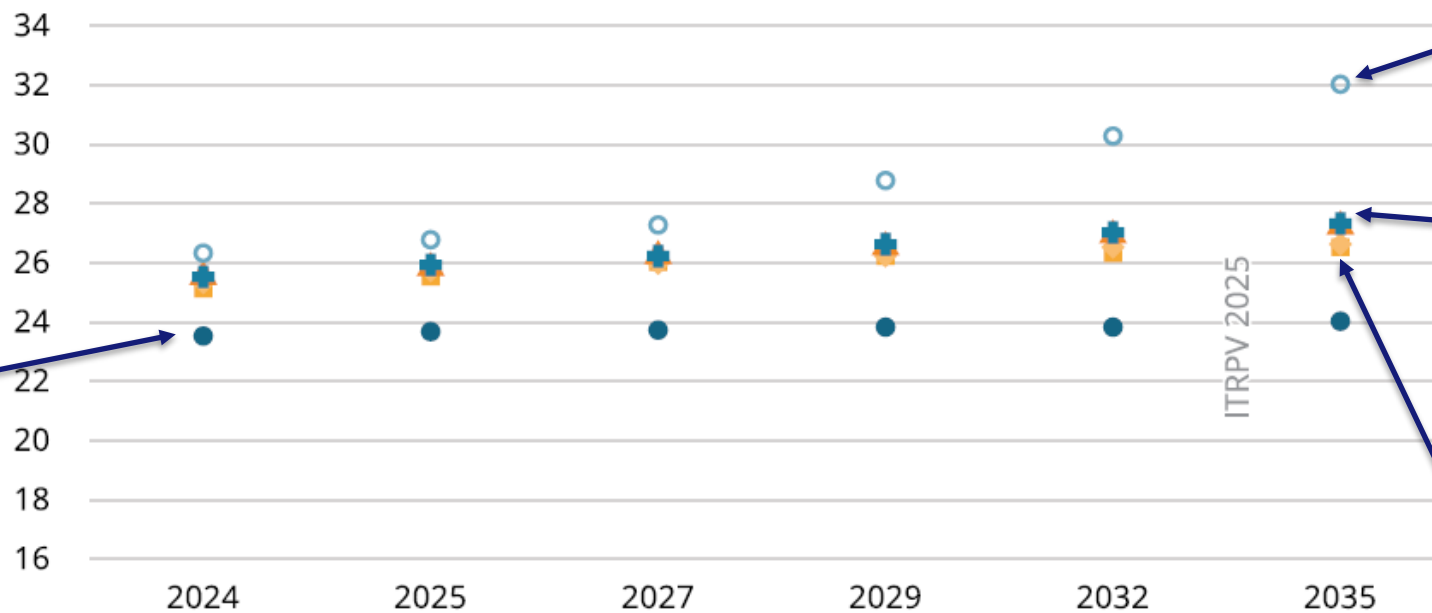


# Solar Cell Evolution

## Average stabilized efficiency values for Si solar cells in mass production

Measured with busbars (no BB-less measurement) and front side STC

Stabilized cell efficiency [%]



● PERC p-type mono-Si

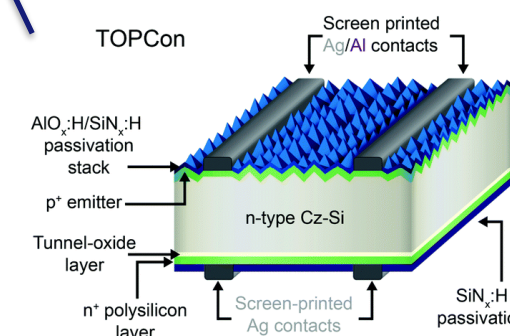
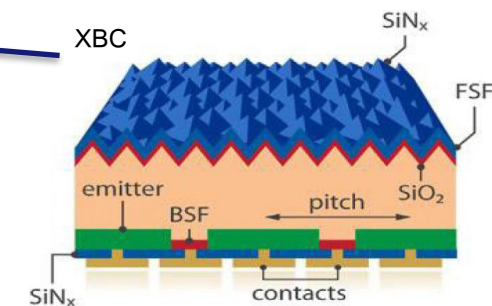
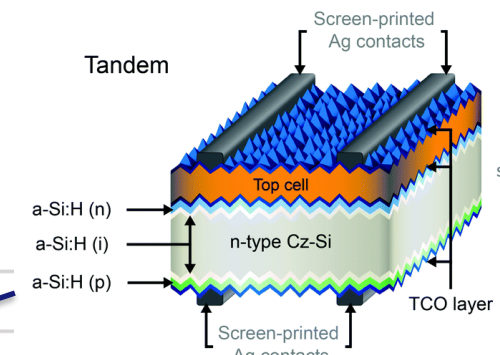
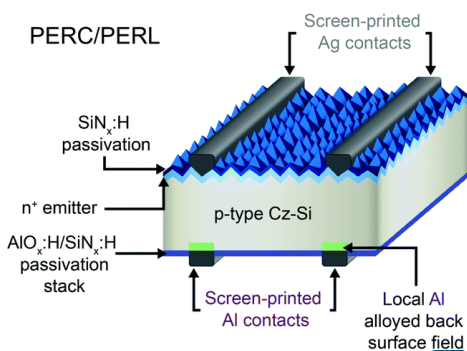
■ TOPCon double sided contact cells (passivated contacts on rear side) n-type mono-Si

◆ Silicon heterojunction (SHJ) double sided contact cells n-type mono-Si

▲ TOPCon-based back contact cells (TBC)

⊕ SHJ-based back contact cells (HBC)

○ Crystalline silicon-based tandem cells

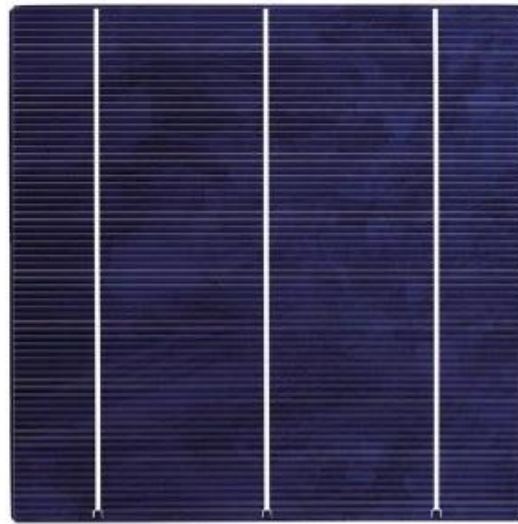


## First generation: Aluminium Back Surface Field (Al BSF) cell

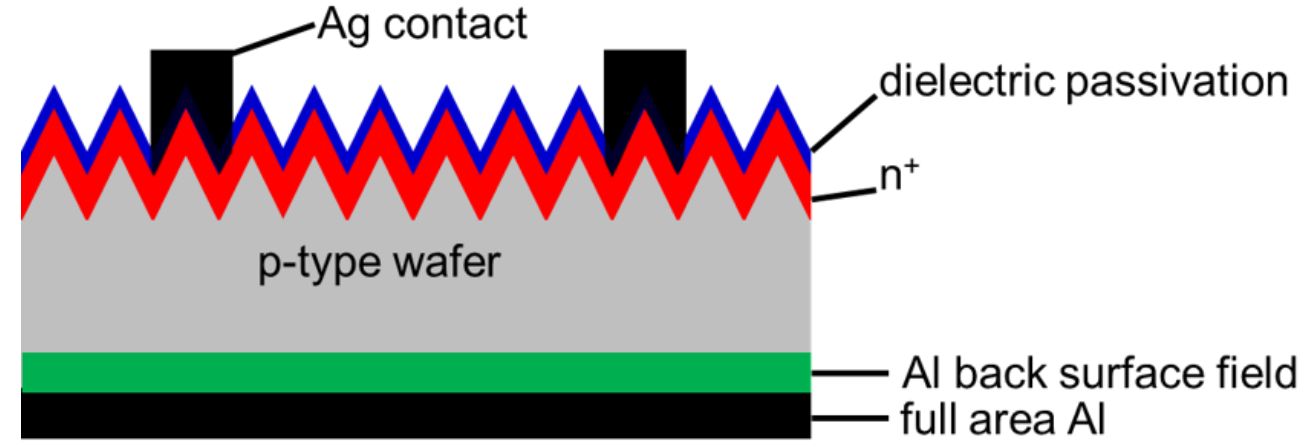
2004–2017



Monocrystalline  
silicon solar cell



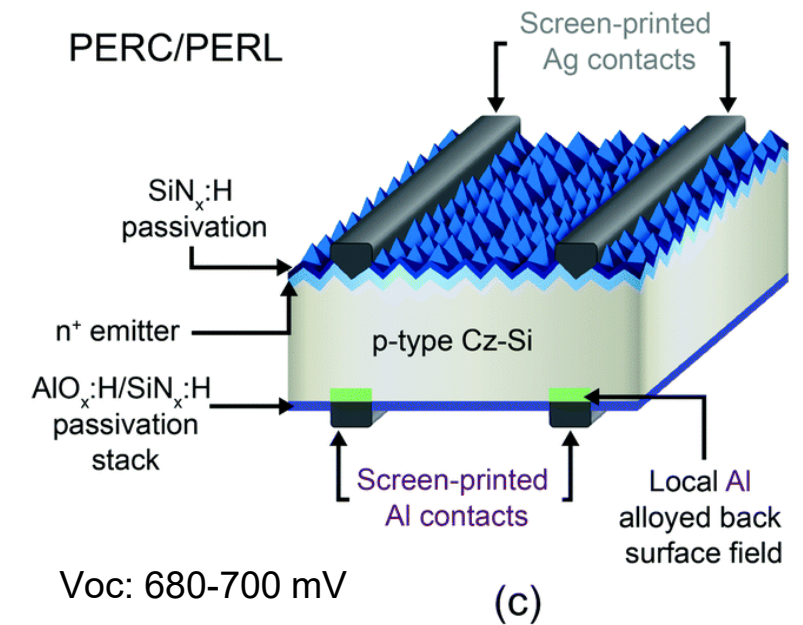
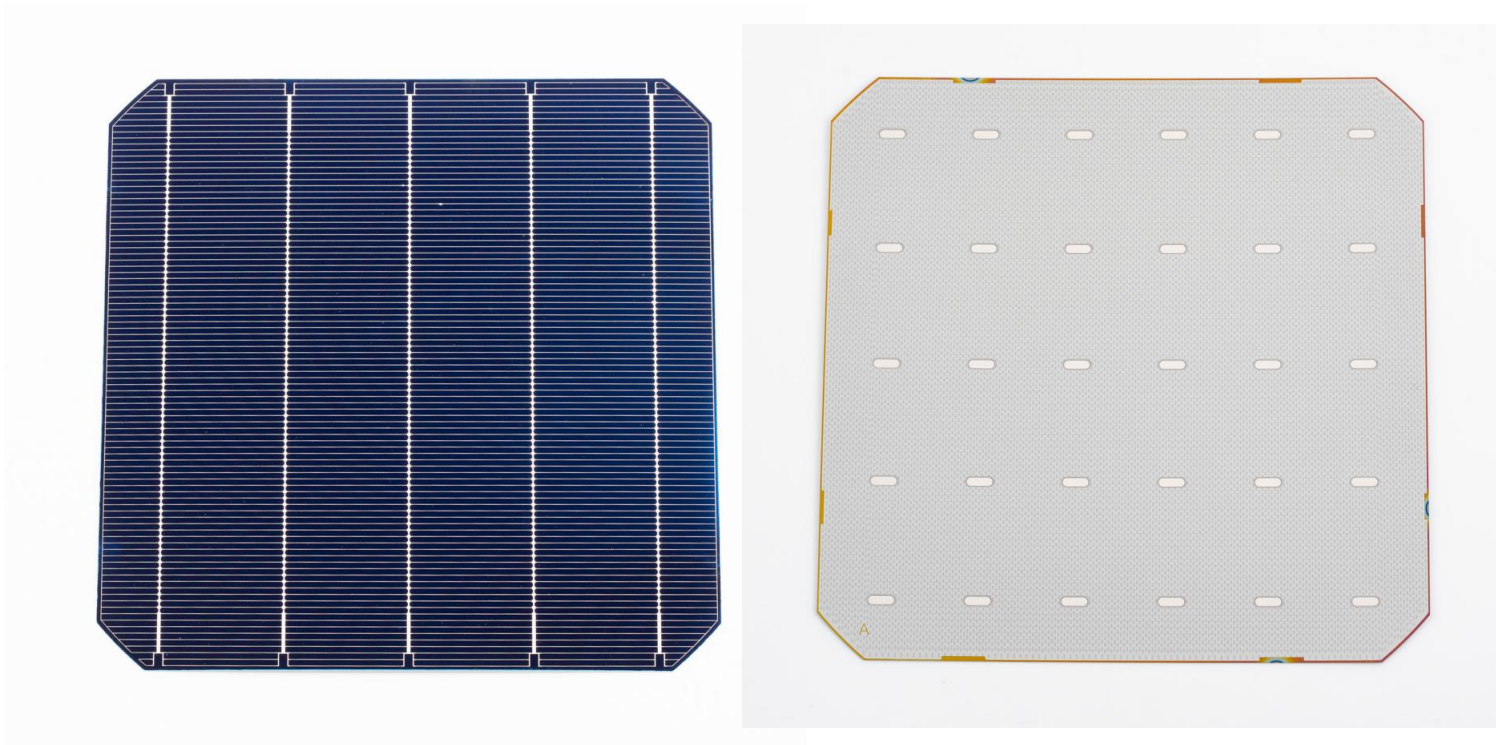
Polycrystalline  
silicon solar cell



Voc: 650 mV

Thickness of the BSF aluminium layer: between 0.7  $\mu\text{m}$  and 1.5  $\mu\text{m}$

## Second generation: PERC (Passive Emitter Rear Cell) cell



Passivation: thickness of the passivation layer,  $\text{AlO}_x$ , approximately 10 nm

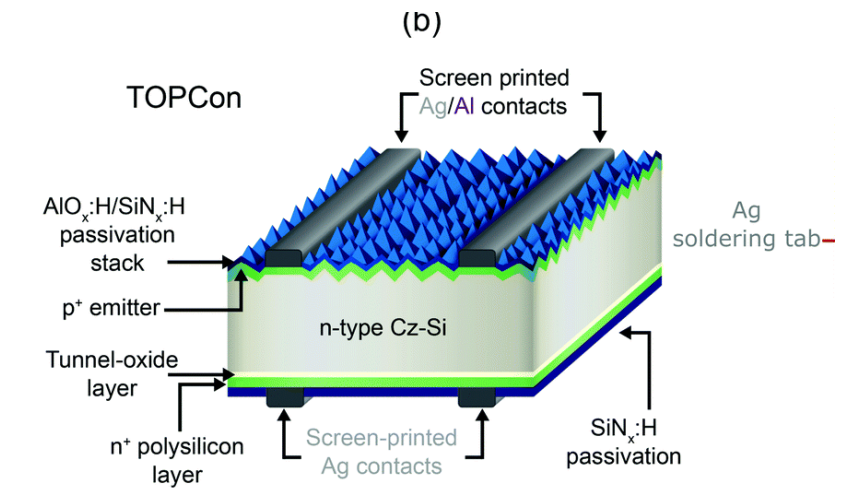
## PERC cell (Passive Emitter Rear Cell): limits

- The widespread doping of the wafer surfaces reduces recombination at the metal/silicon interface, but introduces adverse effects such as :
  - Auger recombination,
  - Absorption of free charge carriers
  - Reduction in the energy bandgap
- These phenomena limit the efficiency of traditional solar cells.

### **Solution: Carrier Selective Passivating Contacts (CSPC)**

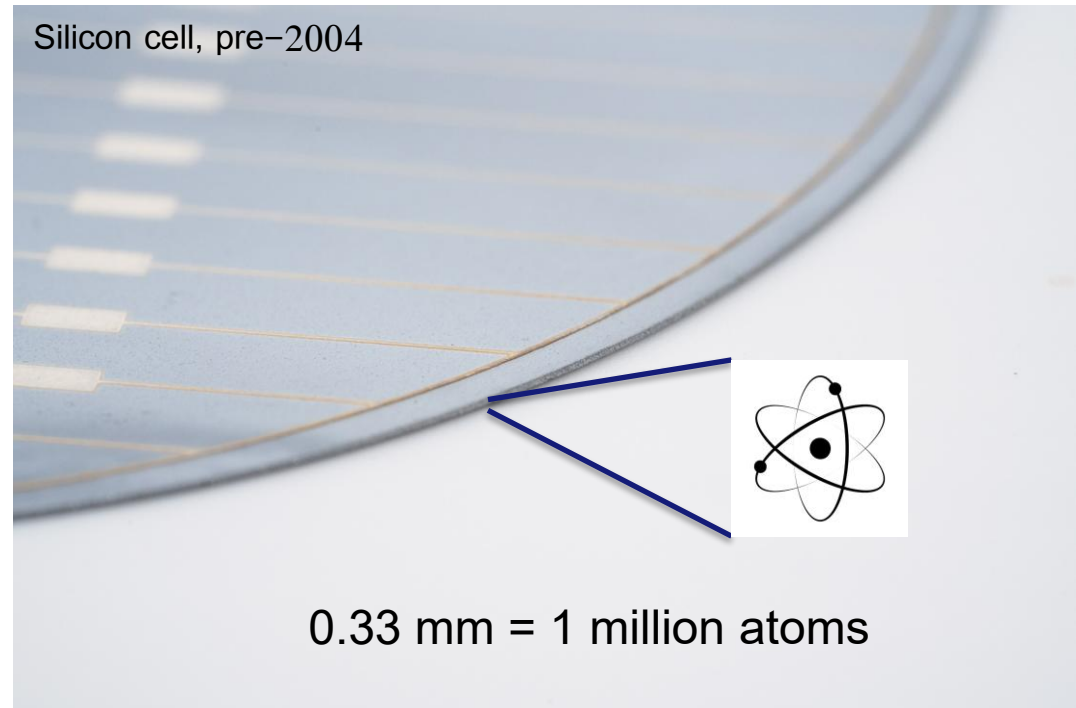
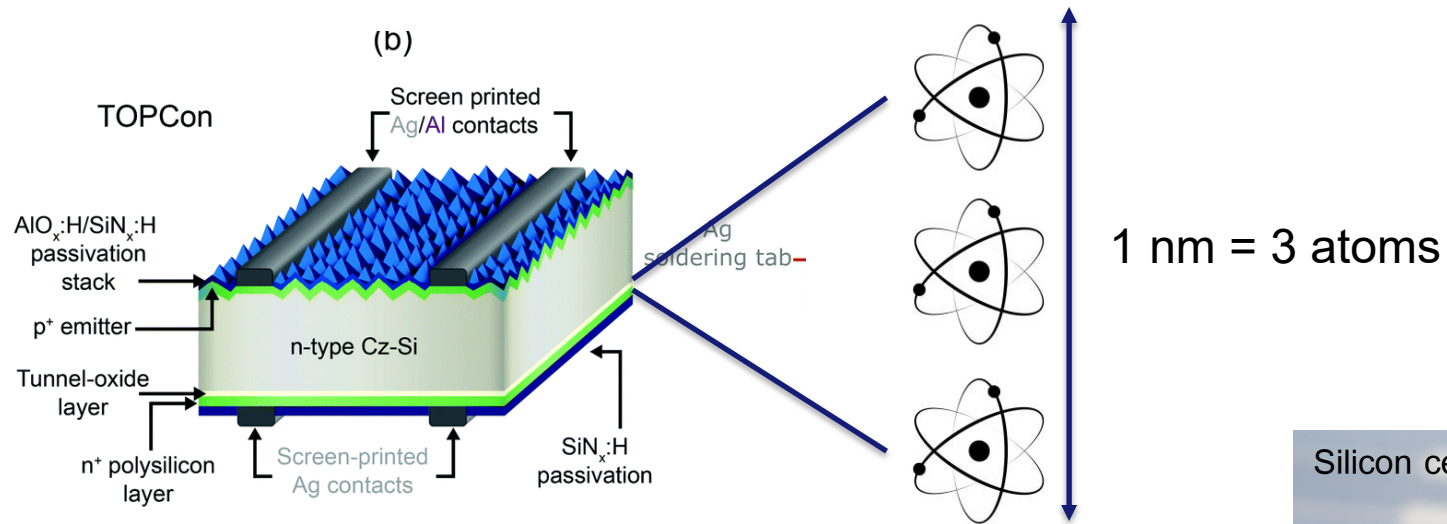
- Designed to eliminate direct metal-to-silicon contact.
- They consist of thin layers deposited on both sides of the wafer:
  - They passivate the surface defects.
  - They selectively collect the photogenerated carriers.

## Third generation: TOPCON cell

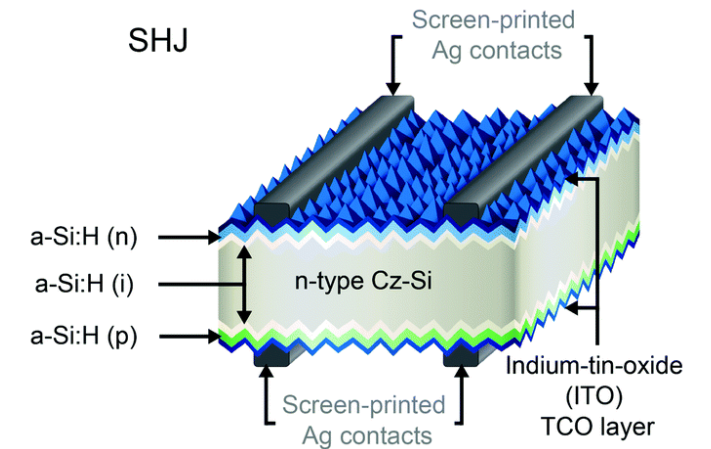
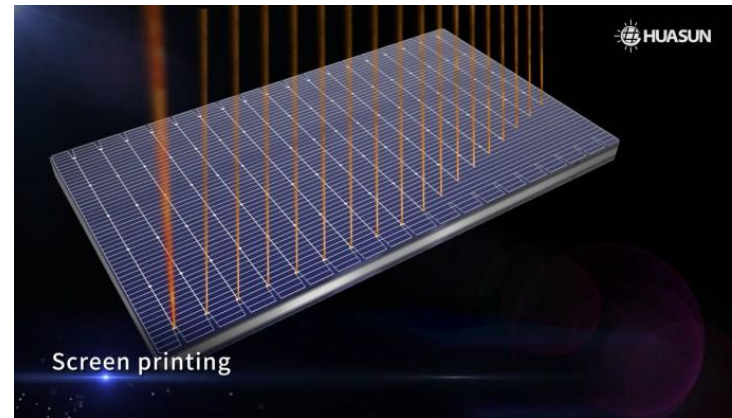
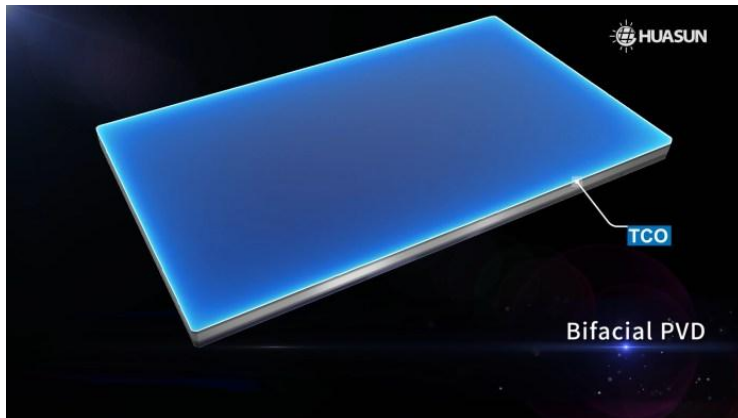
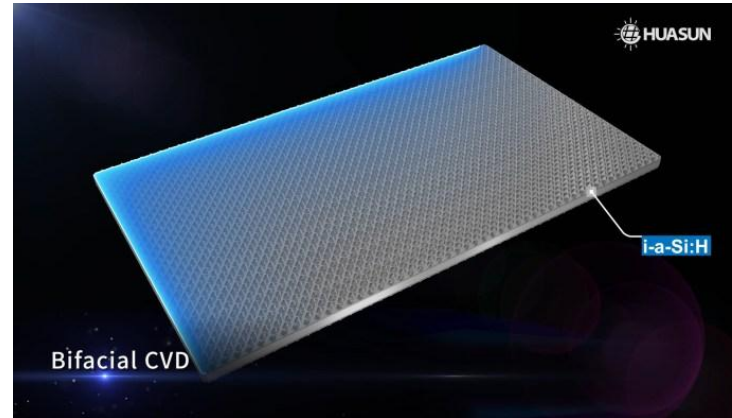


Voc: 715 mV Bifacial cell

Passivation:  $\text{SiO}_x$  oxide tunnel layer thickness 1–2 nm, polysilicon 50–300 nm

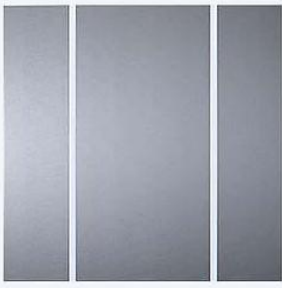
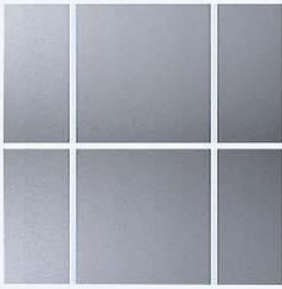


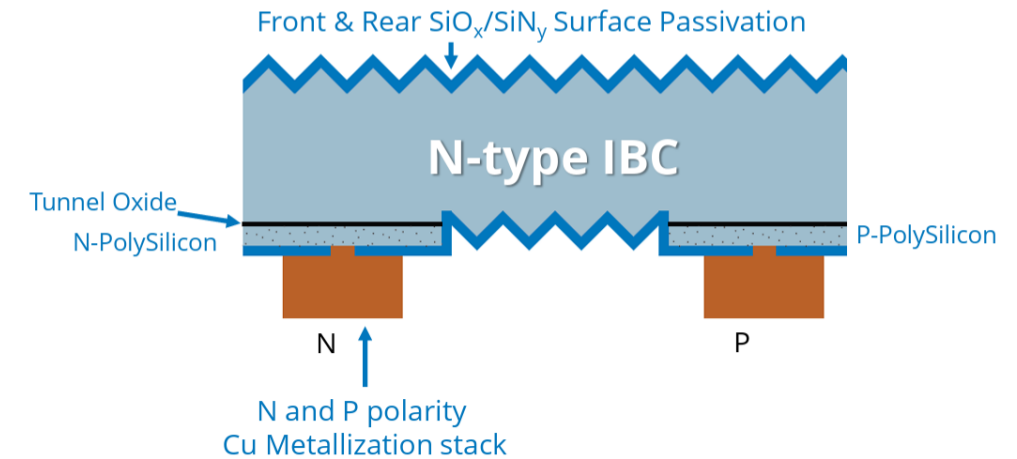
## Third generation: heterojunction cells



Voc: 740 mV Bifacial cell

## Third generation: Interdigitated Back Contact (IBC) cells: Maxeon

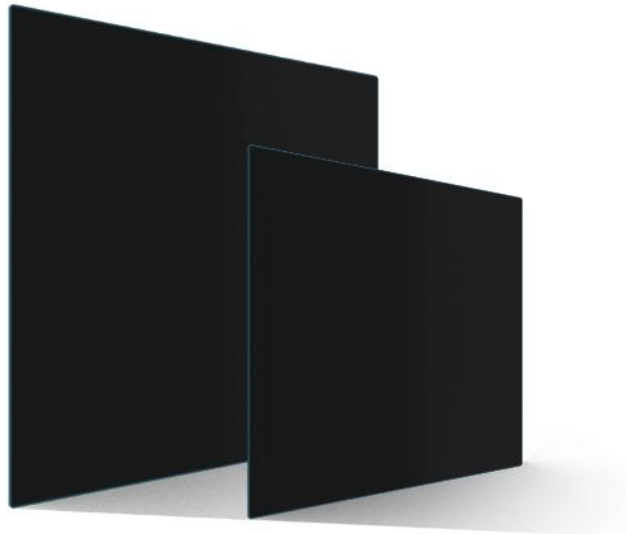
|                                                                                                                                                                                                                          | SunPower® Maxeon Cell                                                              | vs | Conventional Cell                                                                   |                                                                                                                                                                                                                              |
|--------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|------------------------------------------------------------------------------------|----|-------------------------------------------------------------------------------------|------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| <br><b>No Grid Lines on Front of Cell</b><br>Maxeon cells absorb more sunlight and look incredible on roof.                             |   |    |   | <br><b>Lines of Metal Paste on Front of Cell</b><br>Power output drops as the thin paste reflects light and corrodes.                     |
| <br><b>Solid Copper Backing</b><br>Our thick copper foundation adds massive strength and is almost impervious to corrosion.             |   |    |   | <br><b>Even More Metal Paste on Back of Cell</b><br>Offers no strength. Cell can crack and lose power when exposed to temperature swings. |
| <br><b>Thick Connectors</b><br>Expanding and contracting from daily temperature swings are no problem with our built-in strain relief. |  |    |  | <br><b>Thin, Weak Connections</b><br>Lose just one of these narrow ribbons and the entire cell fails.                                    |



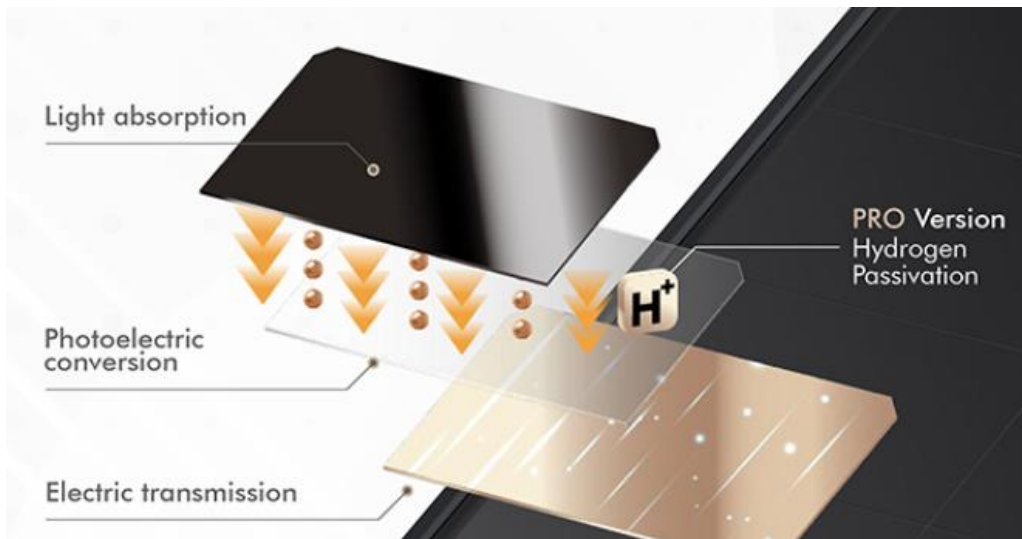
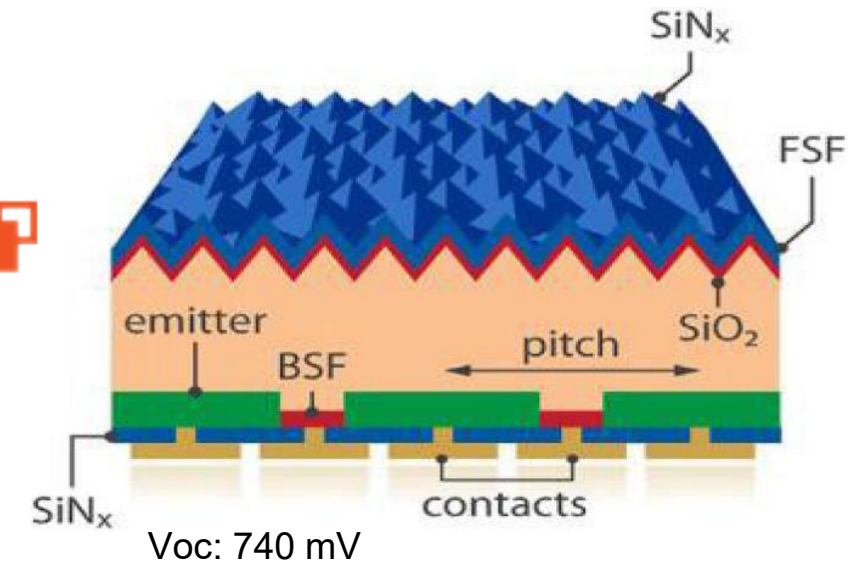
Voc: 740 mV

**maxeon**

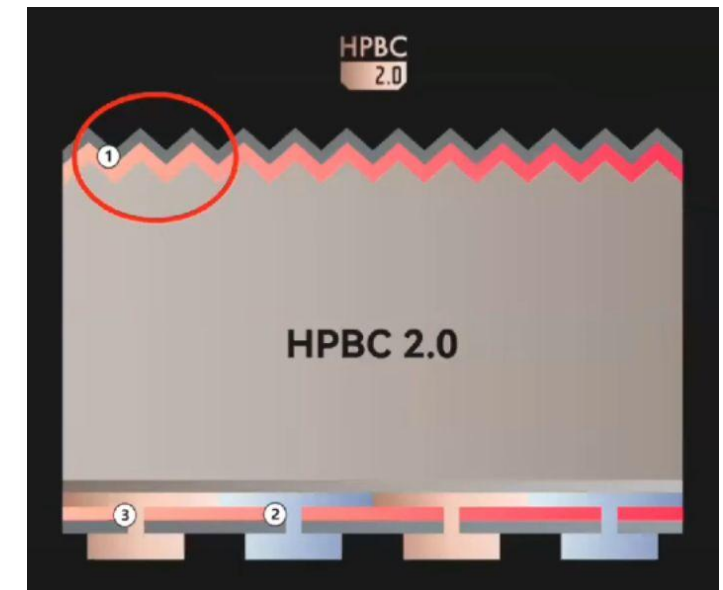
## Third generation: All Back Contact (ABC) cells / Hybrid Passivation BC 2.0: AIKO / Longi



**AIKO**



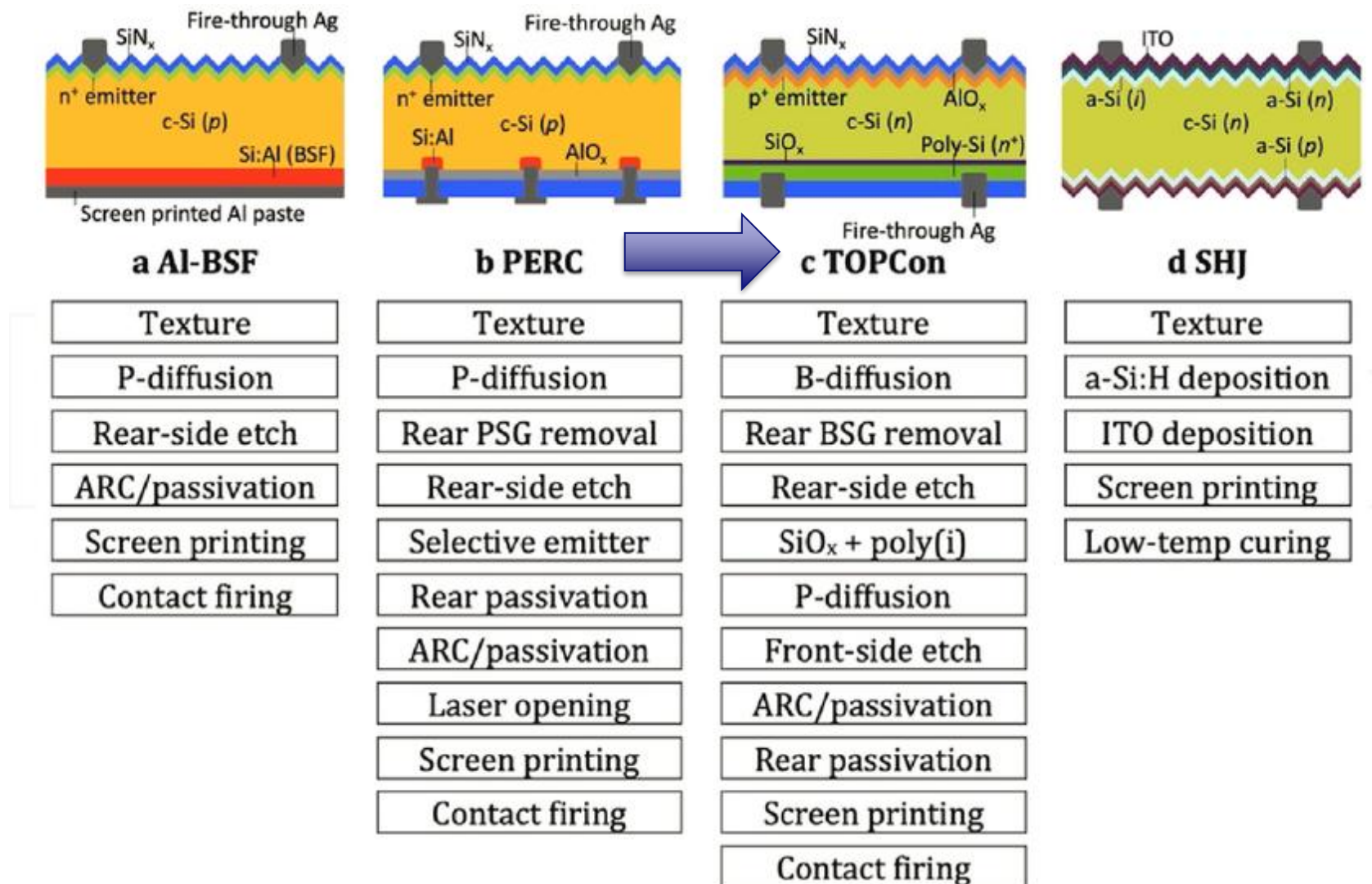
**LONGI**



## Third generation plus: TOPCon-compatible hybrid back-contact (THBC) / Hybrid Interdigitated-Back-Contact (HIBC) Trina/Longi



# Industrial competitiveness: upgrading production lines from PERC to TOPCON



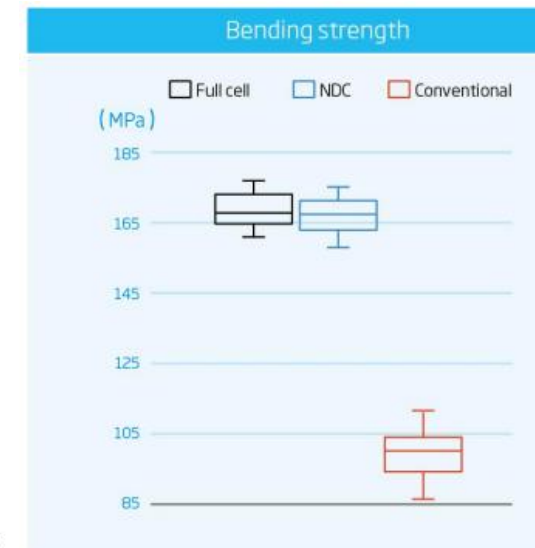
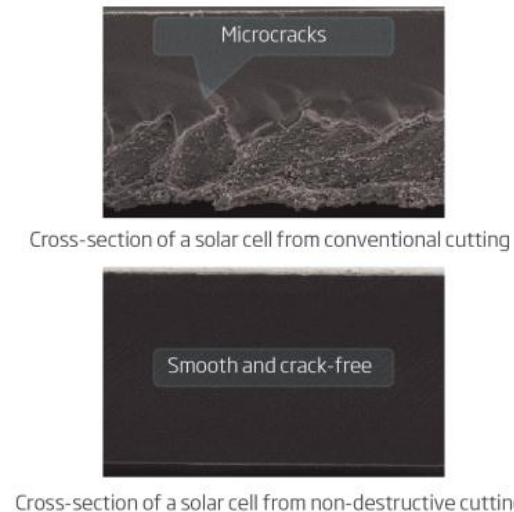
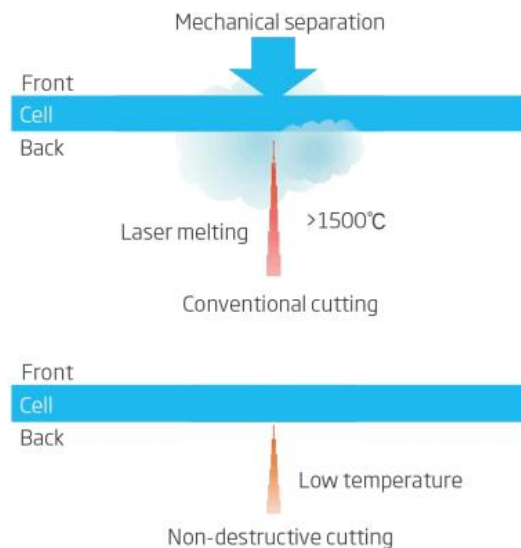
# Making PV Modules...

## Cell cutting (Full-cell to 1/2, 1/3 and shingled cells)

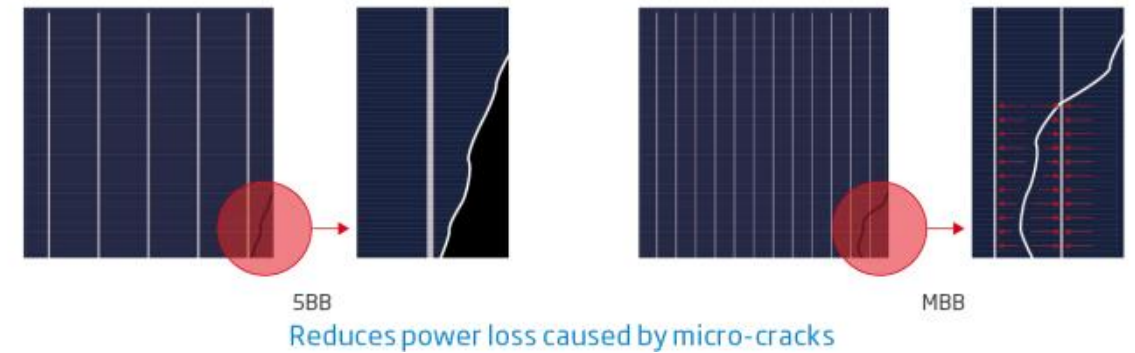
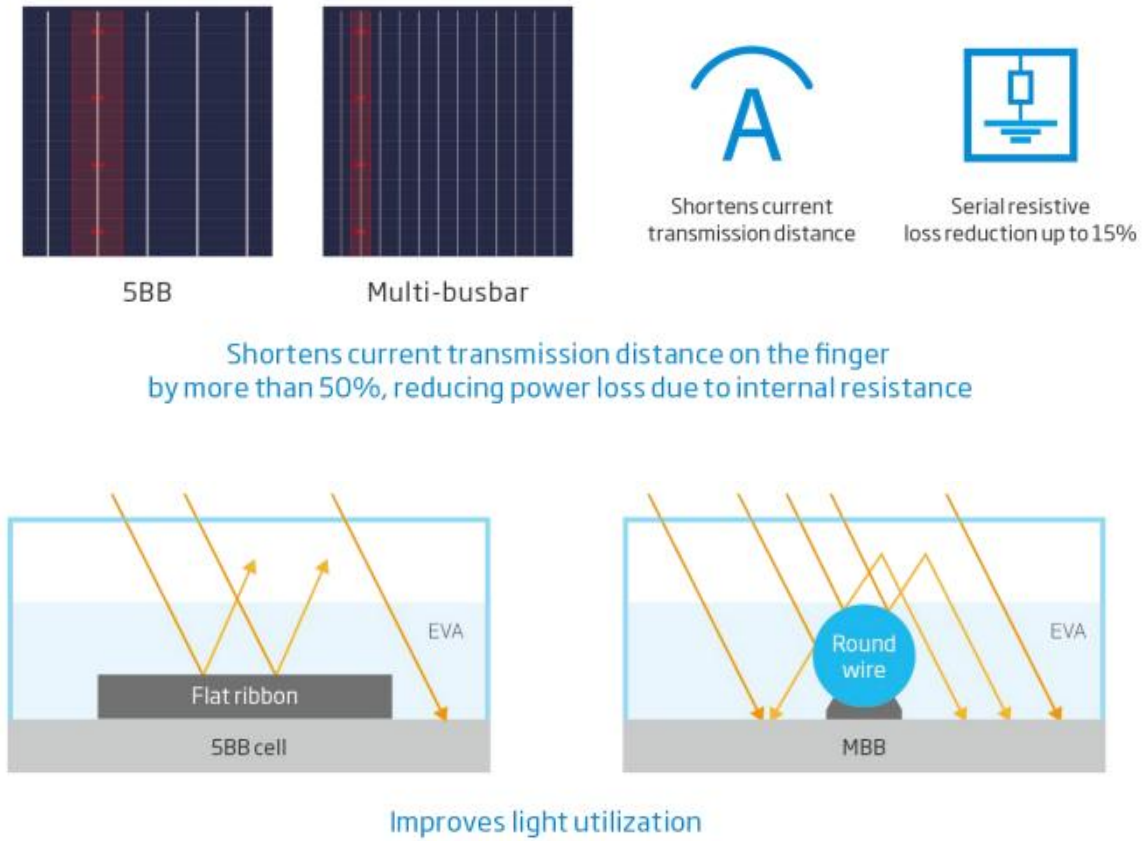
| Technology ( <i>only most common ones</i> )   | Working Principle                                                    | Main Advantages                                         | Main Challenges                       | Typical Applications                |
|-----------------------------------------------|----------------------------------------------------------------------|---------------------------------------------------------|---------------------------------------|-------------------------------------|
| <b>Laser Scribing + Mechanical Separation</b> | Laser creates weakened line, followed by controlled mechanical break | High throughput, mature process, cost-effective         | Microcracks, heat-affected zone       | Mainstream PERC / TOPCon production |
| <b>Thermal Laser Separation (TLS)</b>         | Local heating and cooling generate controlled crack propagation      | Very low damage, smooth edges, high mechanical strength | Higher equipment cost, slower process | High-efficiency TOPCon / HJT        |
| <b>Full Laser Cutting</b>                     | Laser cuts completely through wafer                                  | High precision, flexible geometries                     | More thermal damage and debris        | Shingled cell manufacturing         |

Transition toward low-damage laser processes. Increasing adoption driven by:

- thinner wafers
- larger wafer formats
- high-efficiency cell technologies
- shingled module architectures



## Multi Busbars

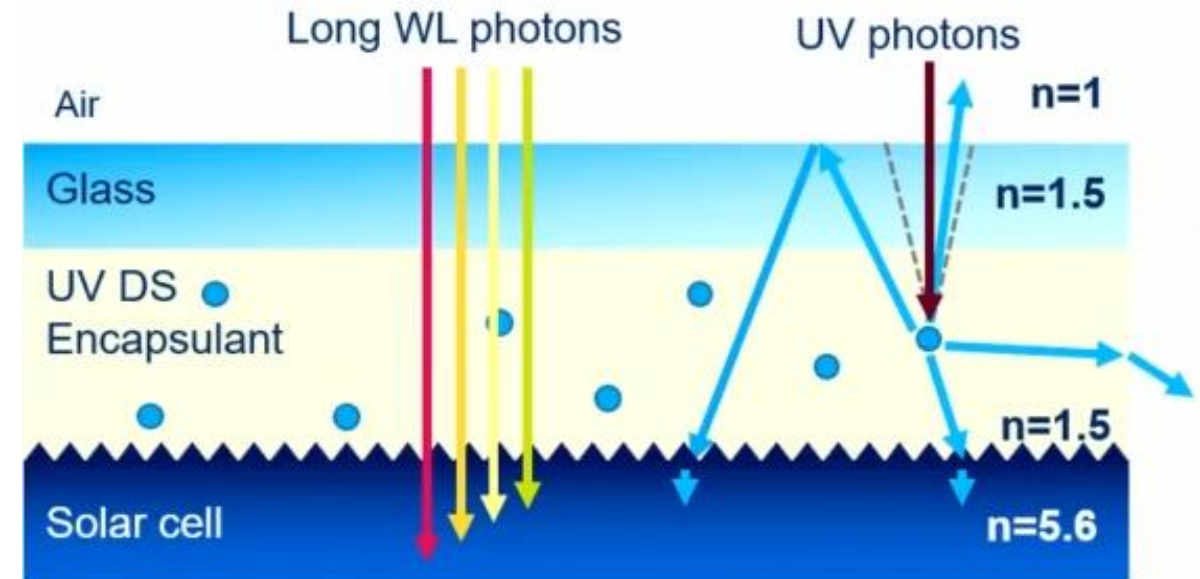


## UV-Downshifting Encapsulants

UVID Mitigation: Specifically addresses UV-induced degradation in high-efficiency c-Si cells by shifting high-energy photons to lower energies, which also reduces parasitic absorption.

Efficiency gain: Converts UV light into harmless visible light, boosting module power (increased current density)

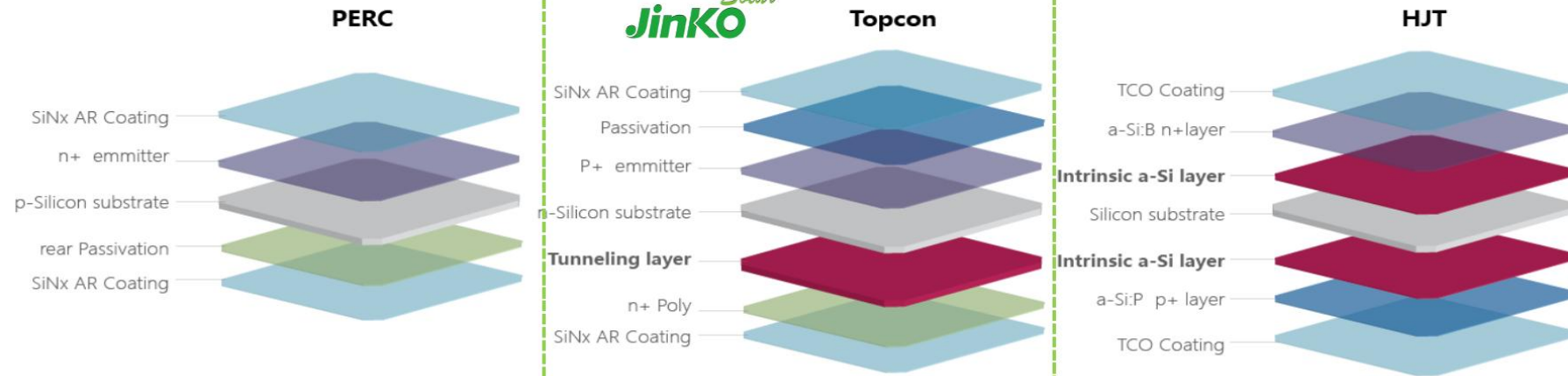
Improving both reliability and power efficiency



L. Marthey et al., EUPVSEC 2025

New cells, new materials, new modules:  
manufacturers' roadmaps.

# Technical Roadmap: Why TOPCon?



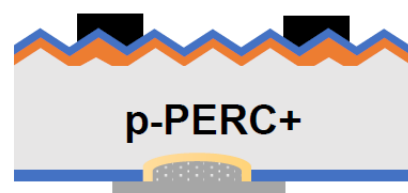
|                                                  |        |              |                  |
|--------------------------------------------------|--------|--------------|------------------|
| Theoretical Ultimate Efficiency <sup>[1,2]</sup> | 24.5%  | <b>28.7%</b> | 28.5%            |
| Temperature Coefficient                          | ~-0.34 | ~-0.29       | <b>~-0.27</b>    |
| Bifaciality                                      | ~70    | ~80          | <b>~85</b>       |
| PID Risk                                         | PID-p  | PID-p        | PID resistant    |
| Delamination Risk                                | Low    | Low          | <b>High</b>      |
| Moisture Sensitivity                             | **     | ***          | <b>*****</b>     |
| Hot Spot Risk                                    | **     | **           | <b>*****</b>     |
| Cost                                             | BSL    | ~BSL         | <b>+~3cent/W</b> |

[1] Brendel, R., Rienaeker, M. & Peibst, R. 2016, "A quantitative measure for the carrier selectivity of contacts to solar cells", Proc. 32nd EU PVSEC, Munich, Germany, doi:10.4229/EUPVSEC201620162CO.4.1.

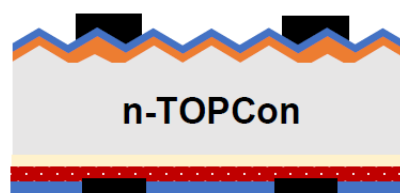
[2] Brendel, R. & Peibst, R. 2016, "Contact selectivity and efficiency in crystalline silicon photovoltaics", IEEE J. Photovolt., Vol. 6, No. 6, pp.1413–1420, doi:10.1109/JPHOTOV.2016.2598267.

# Efficiency pradox, struggle for BC future

Solar Cell Efficiency Tables (Version 65) 21/10/2024



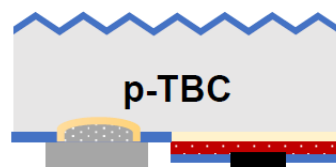
694mV, 24.0%, 07/2019



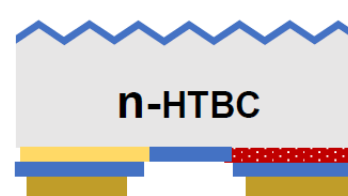
744mV, 26.58%,  
11/2024



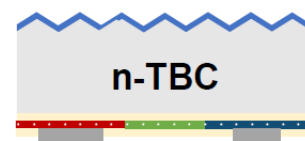
751.4mV, 26.8%,  
10/2022



733mV, 25.5%  
lab data



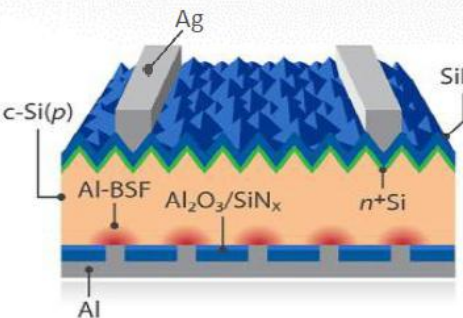
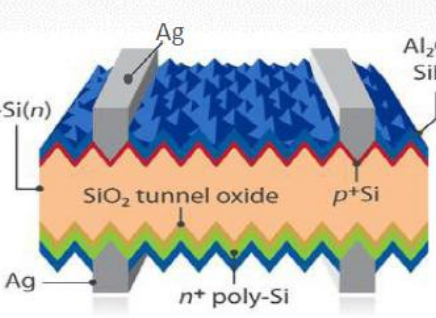
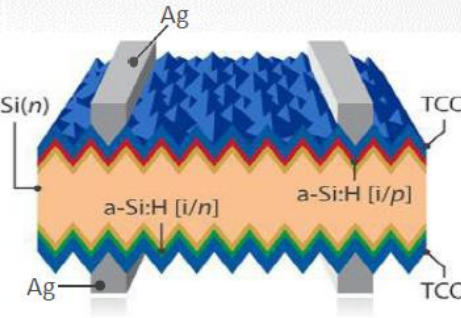
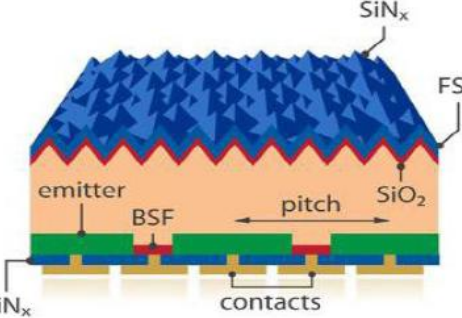
745.6mV, 27.4%,  
09/2024



744.7mV, 27.0%  
08/2024

- Ag
- Al
- Al-BSF
- Diffusion layer
- p-Si
- dielectric
- SiOx
- n-polySi
- p-polySi
- i-polySi
- a-Si/nc-Si
- Cu

# Comparison of Solar Cell Technology

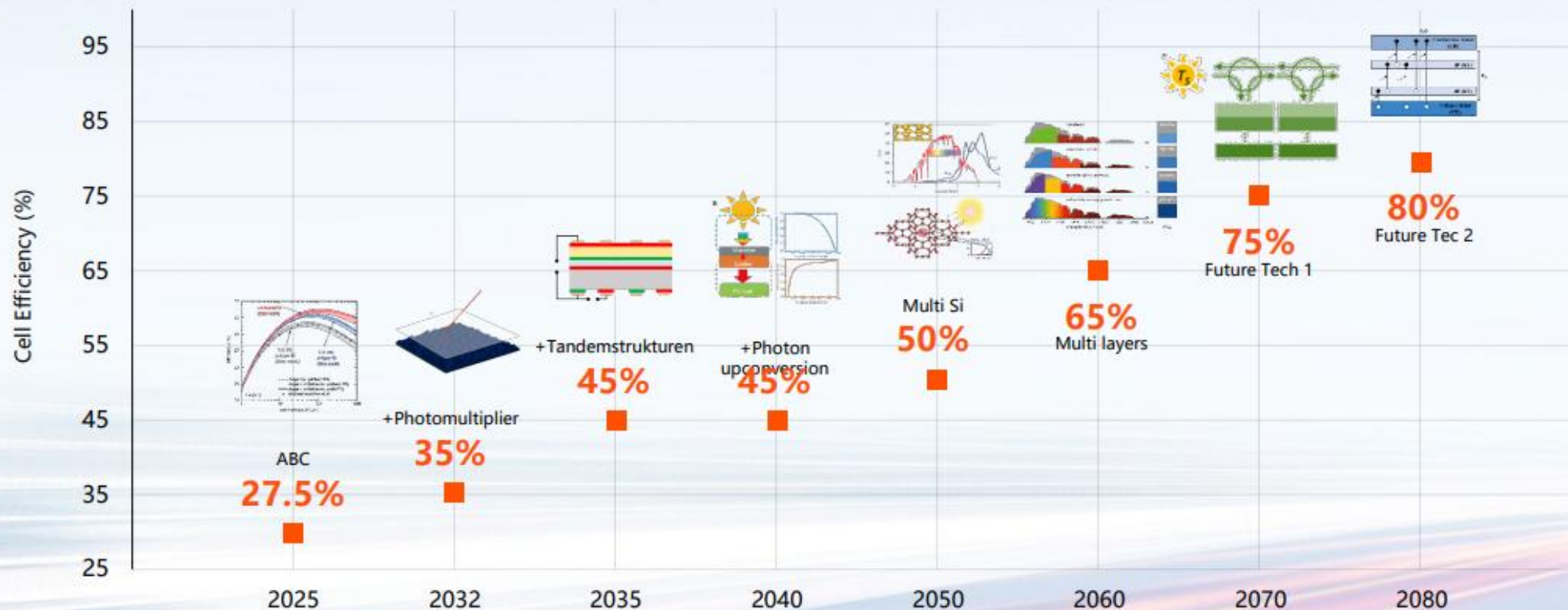
|                          | PERC                                                                              | TOPCon                                                                             | HJT                                                                                 | ABC                                                                                 |
|--------------------------|-----------------------------------------------------------------------------------|------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------|
| Cell Topology            |  |  |  |  |
| Front Surface Shading    | Yes<br>(3-5% Shadings)                                                            | Yes<br>(3-5% Shadings)                                                             | Yes<br>(3-5% Shadings)                                                              | No<br>(0% Shadings)                                                                 |
| Ag-based Metalisation    | Front+Back<br>(~70mg)                                                             | Front + Back<br>(~110mg)                                                           | Front + Back<br>(~150mg)                                                            | No<br>(0mg)                                                                         |
| Metalisation Temperature | >700°C                                                                            | >700°C                                                                             | ~200°C                                                                              | >700°C                                                                              |
| /                        | /                                                                                 | /                                                                                  | /                                                                                   | /                                                                                   |
| Voc                      | 690mV                                                                             | 715mV                                                                              | >740mV                                                                              | >740mV                                                                              |
| ETA Potential            | 23.5-24%                                                                          | 25-26%                                                                             | 25-26%                                                                              | 26-28%                                                                              |

## The Next-gen PV Technology Beyond BC Era



### Two directions for next-generation technology:

- Photon down conversion
- Tandem Technology



Generation Performance

LONGI-高纪-曾子逸 (ZENGZILYI)

LONGI

## BC is Able to Achieve the Highest Efficiency

$$P = I_{sc} * (V_{oc} * FF)$$

Optical( $I_{sc}$ ):**Zero**

Light loss

Electrical( $V_{oc} * FF$ ):**70% +**Reduced current loss+contact resistance<sup>1</sup>**Maximum**

Technology compatibility

## Light Absorption

Multi-layer anti-reflection film and absence of front busbars maximize light absorption and short-circuit current( $I_{sc}$ )

## Photoelectric Conversion

Fully hybrid passivation to boost open-circuit voltage ( $V_{oc}$ ) and fill factor ( $FF$ )

## Electric Transmission

Positive and negative electrodes connected at the back ensure stable current transmission and reduce reliability risk

**29.1%**Highest theoretical cell efficiency among all Si technologies<sup>2</sup>

Note — 1- compared to TOPCon  
2- single-junction crystalline Si cell technologies



## Roadmap of HJT solar cell

HJT + Perovskite Tandem

Tandem

OBB

Larger & Thinner Wafer in Mass Production (G12/G12R-half, 90  $\mu\text{m}$ )

Low Ag Consumption

TCO Composite Film

Passivation

Nano-C/ $\mu\text{C-Si}$

$\alpha\text{-Si}$  Composite Film for Low Damage

2021

24.5%

475 W

M6-144

2022

25.1%

715 W

G12-132

2023

25.5%

735 W

G12-132

2024

26.0%-26.5%

760 W

G12-132

2026

28.0%

800 W

HJT+ Perovskite

## Roadmap of HJT Solar Wafer (SEW)

Half-cut Ingot

Novel Gettering

Tungsten Wire Cut

Granular Silicon

## Roadmap of HJT solar module

Light Management

Flexible/Curved Encapsulation

High-reliability Encapsulation

High-precision SMBB

High-bifaciality Module

OBB Soldering

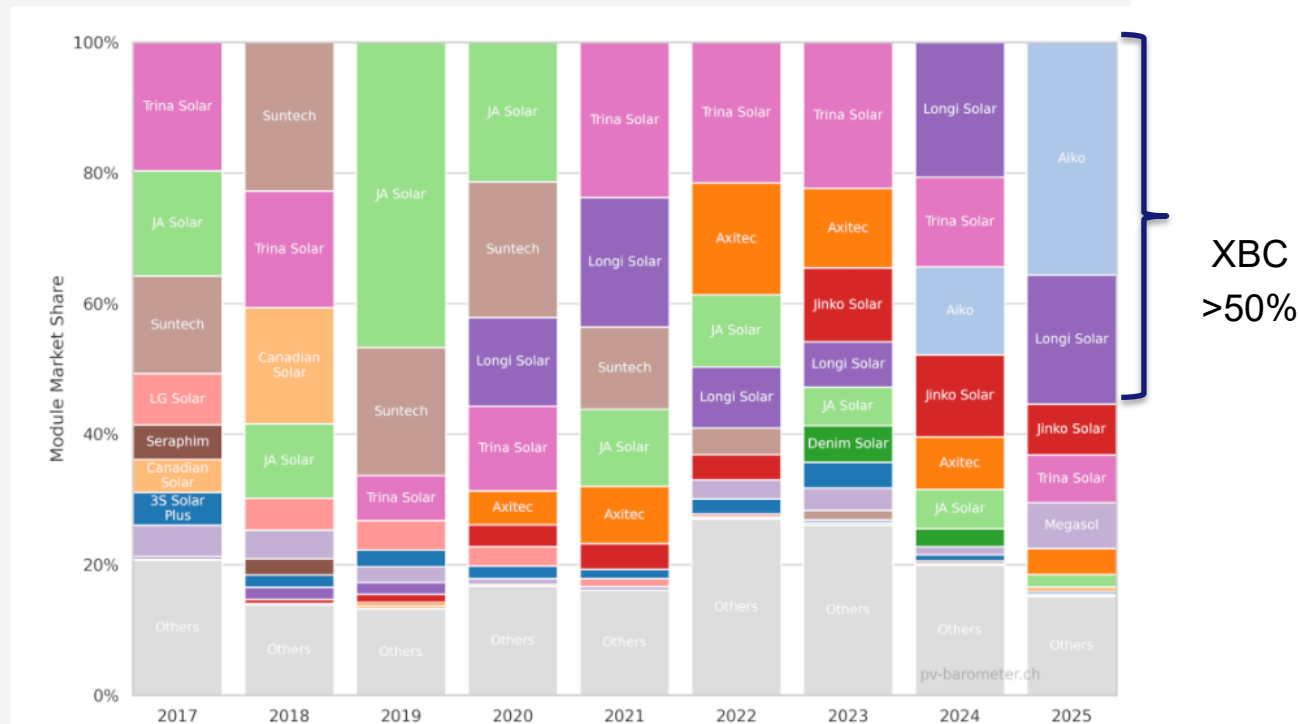
Corrosion-resistant Module for Offshore PV



## Switzerland PV Module Market Share

### Solartrends, Brancheneinblicke und Analysen

Dieser Report zeigt, wie sich die technischen Eigenschaften von PV-Modulen und Wechselrichtern in den Jahren 2017 bis 2025 verändert haben. Darüber hinaus wird auch die Entwicklung von System- und Marktdaten wie Marktanteile von Herstellern oder die Anzahl Batteriespeicher analysiert. Die Daten stammen aus einer anonymisierten und mengengewichtet konsolidierten Datenbank von Eternity und wurden gemeinsam mit dem PV-Labor der Berner Fachhochschule (BFH) aufbereitet. Es wird angenommen, dass die vorgestellten Produktdaten repräsentativ für PV-Anlagen in der Schweiz und generell für PV-Anlagen auf Gebäuden sind. Freiflächenanlagen hingegen sind in den Daten kaum vertreten.



## Summarising:

- Solar cells and their efficiency are evolving rapidly and continuously: today, we have modules for residential installations with a capacity of over 500W.
- On the Swiss and European residential markets, the size of the panels is limited only by their weight: the switch to glass-to-glass solutions results in weights exceeding 25 kg, which poses a problem for handling
- The potential of IBC cells is also promising due to their intrinsic diode effect at the single-cell level: in the event of shading, losses are lower and temperatures are lower
- Topcon's technology is based on PERC technology, which has been on the market for several years
- The potential of bifacial cells is of interest for large modules and large-scale projects, but it also influences choices in the residential market
- With so many changes, it is easy to lose sight of the factors that ensure the quality of the modules: accelerated testing, field testing, in-line quality control, and the ability to rectify errors without the risk of going bankrupt, as has happened in the past.

# Thank you!